

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	{100} +/- 1	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Length	18.00 +/- 2.00 mm @ 90+- 5 deg	
	5.0	Overall Thickness	381.00 +/- 7.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00 μ m	Guaranteed by Process
	7.0	Bow	<40.00 μ m	ADE to ASTM F534, 20%
	8.0	Warp	<40.00 μ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	None	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Frontsurface condition	Polished	Bright Light, 100% (note2)
	12.0	Backsurface condition	Polished with lasermark and light handling marks	Bright Light, 100% (note2)
	13.0	Handle Silicon Raw Material	Prime Silicon	
	14.0	Handle Growth Method	CZ	Wafer Vendor
	15.0	Handle Orientation	{100} +/- 0.5	Wafer Vendor
	16.0	Handle Thickness	381.00 +/- 7.00 μ m	ADE, 100%
	17.0	Handle Doping Type	P	Wafer Vendor
	18.0	Handle Dopant	Boron	Wafer Vendor
	19.0	Handle Resistivity	>30	Wafer Vendor
	19.1	Handle Silicon Dislocation Etch Pit Density	<100/cm ²	Wafer Vendor
	20.0	Surface Haze	None	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information